IC for Headphone Stereos Monolithic IC MM1104

August 6, 1994

Outline

This IC was developed for use in 3 V headphone stereos. It incorporates all the basic functions of tape players.

Mitsumi has previously offered the LAG665, LAG668, LAG673 and MM1006 as one-chip versions. However, this IC is the result of a through review and redesign extending to circuit details.

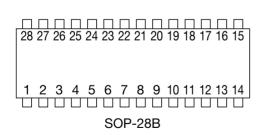
Features

- 1. Configuration: Pre-and power amp, motor control
- Adoption of shock noise prevention circuitry Through the use of a circuit which suppresses noise occurring when the power supply is turned on and off, noise output is reduced without muting.
- Stable motor speed control circuit
 A bridge circuit employing power transistors provides motor speed control with minimal drift.
- 4. Preamp off pin is convenient for radio connections
- 5. Radiation pin: When radio wave-induced noise is a problem, this pin can be used to cut the frequency characteristic.

Package

SOP-28B (MM1104AF, MM1104BF, MM1104CF)

Pin Assignment



1	1/2Vcc	15	N.C
2	Prein1	16	Speed
3	NFB1	17	Phase
4	PreOUT1	18	Vs
5	Pre Off	19	PowerOUT2
6	Powerin1	20	Amp Vcc
7	Radiation1	21	Filter
8	PowerOUT1	22	Radiation2
9	GND	23	Powerin2
10	Governor Vcc	24	N.C
11	N.C	25	PreOUT2
12	PCOUT	26	NFB2
13	GND	27	Prein2
14	Governor GND	28	Amp GND

Absolute Maximum Ratings

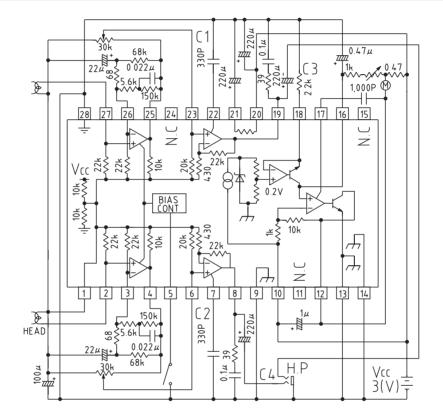
Item	Symbol	Ratings	Units	
Operating temperature	Topr	-20~+65	°C	
Storage temperature	Tstg	-40~+125	°C	
Power supply current	Vcc	-0.3~+7.5	V	
Power consumption	Pd	700 (Ta=25°C)	mW	
Operating voltage	Vop	+2.0~+5.0	V	

Electrical Characteristics (Except where noted otherwise, Ta=25°C)

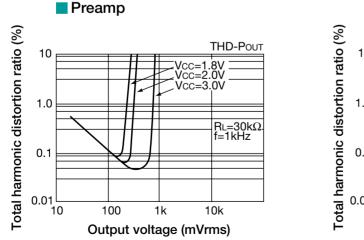
Item	Symbol	Measurement conditions	Min.	Тур.	Max.	Units		
Consumption current	Icc	Amp. only		11	18	mA		
Preamp unit (Ta=25°C)								
Open-circuit gain	GVo	Vo=-10dBm f=100Hz		86		dB		
Closed-circuit gain	osed-circuit gain GVc Vo=-10dBm			42		dB		
Maximum output voltage	Vom	THD=10%	0.5	0.74		Vrms		
Total harmonic distortion ratio	THD	Vo=-10dBm		0.06	0.5	%		
Output noise voltage	Vno	Rg=2.2kΩ, CCIR waiting		240	500	μVrms		
Crosstalk between channels	СНст	Vo=-10dBm		60		dB		
Ripple rejection	RR	Vcc=3V, VR=-20dBm, fr=100Hz	30	42		dB		
Output voltage with preamp off	VoOff	Vo=–10dBm, when pre operation		-100	-70	dBm		
Input resistance with preamp off	RiOff		7	10	13	kΩ		
Output resistance with preamp off	RoOff		7	10	13	kΩ		
Measurement conditions: Except where noted otherwise, Vcc=3V, Rg= $2.2k\Omega$, RL= $30k\Omega$, f= $1kHz$								
Power amp unit (Ta=25°C)								
Input resistance	Ri	i		20	26	kΩ		
Voltage gain	Voltage gainGvPo=5mW		32	34	36	dB		
Voltage gain difference between channels	⊿Gv			0	2	dB		
Maximum output power I	Pom1	THD=10%, RL=16Ω		62		mW		
Maximum output power II	Pom2	THD=10%, RL=32Ω		34		mW		
Total harmonic distortion ratio	harmonic distortion ratio THD Po=5mW			0.4	2	%		
Crosstalk between channels	СНст	Po=5mW	45	62		dB		
Output noise voltage	Vn	Rg=1kΩ, CCIR waiting		150	300	μVrms		
Ripple rejection	RR	Vcc=3V, Vr=-20dBm, fr=100Hz	40	50		dB		
Measurement conditions: Except where noted otherwise, Vcc=3V, Rg=1kΩ, RL=16Ω, f=1kHz								
Motor governor (Ta=25°C)								
Consumption current	Id	A2 measured		2.0	7.0	mA		
Startup current	Iмs	Ім measured when $Rv=1.5\Omega$	500			mA		
Reference voltage	Vref	V5 measured with SW12 off	0.09	0.10	0.11	V		
Reference voltage fluctuation I	⊿Vref1	VS fluctuation for		0.1	0.5	%/V		
		Vcc=1.5 to 3.5V, Vcc=3.0V ref.			0.0	707 V		
Reference voltage fluctuation II	⊿Vref2	VS fluctuation for	0.005		0.05	%/mA		
		Iм=25 to 200m A, Iм=100mA ref.			0.05	/0/ 11// 1		
Reference voltage fluctuation III	⊿Vref3	VS fluctuation for	0.01			%/°C		
		Ta= -10 to 60° C, Ta= 25° C ref.				/0/ C		
Output saturation voltage	VoSAT	Reference voltage V8 measured	0.2		0.3	V		
		IM=200mA with SW12 on		0.2		v		
Bridge ratio	K	V7/V6 measured	9	10	11			

Item	Symbol	Measurement conditions	Min.	Тур.	Max.	Units	
Bridge ratio fluctuation I	⊿K1	K fluctuation for		0.1	0.2	%/V	
Bhuge faile fluctuation f		Vcc=1.5 to 3.5V, Vcc=3.0V ref.					
Bridge ratio fluctuation II	⊿K2	K fluctuation for	0.05		0.2	%/mA	
bildge faile incluation if		IM=25 to 200m A, IM=100mA ref.		0.05	0.2	/0/ IIIA	
Bridge ratio fluctuation III	⊿K3	K fluctuation for		0.01		%/°C	
Bhuge ratio nuctuation in		Ta=-10 to 60°C, Ta=25°C ref.	0.01			/0/ C	
Measurement conditions: Except where noted otherwise, Vcc=3V, IM=100mA, SW11=OFF, SW12=ON							

Block Diagram (Example of Application Circuits)



Characteristics



Power amp

